RELIABILITY MONITOR

PRODUCT	MONITOR DATE	DATE CODE	ASSEMBLY FACILITY	ASSEMBLY LOT NO	PROCESS TYPE	PACKAGE TYPE
DS1669	May-97	9706 B3	OMEDATA	DD642765ABA1	1.2µ OX/NI EEPROM	08 SOIC 208

STRESS/JOB NO.		READPOINT (Sample Size/No. of Fails)		
Preconditioning (P/C): HTC Vapor Phase P-19656			Electrical 235/0	Cum % 0.0%
Infant / High Voltage Life ** 125°C, 7.0 V. P-19807, P-19831	48 Hr 227/0	336 Hr 77/0	1KHr 77/0	*Failure Rate 30 Fits
Temp Cycle -55°C to +125°C P-19832		300 ~ 35/0	1K ~ 35/0	Cum % 0.0%
Biased Moisture 85°C/85% RH, 5.5 V. P-19833		274 Hr 75/0	959 Hr 75/0	Cum % 0.0%
Storage Life 150°C, No bias P-19834	0 Hr 38/0 Write Data	336 Hr 38/1 F1	1KHr 35/0	Cum % 2.6%

*Chi Squared Method, 60% C. L., 55°C & 5.5V; Temperature Derating: Ea = 0.7 ev; Voltage Derating B = 1.0

** with Write Cycle Program stress = 60~/hr/cell

Failure Mode	**Failure Analysis**
F1: Read EEPROM	In process, 970213

DL, 11/5/97